

Hiroki Hibino

List of Publications by Year in descending order

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81900

39
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82547

72
g-index

247
all docs

247
docs citations

247
times ranked

7794
citing authors

#	ARTICLE	IF	CITATIONS
1	Single-Walled Carbon Nanotube Growth from Highly Activated Metal Nanoparticles. Nano Letters, 2006, 6, 2642-2645.	9.1	413
2	Microscopic thickness determination of thin graphite films formed on SiC from quantized oscillation in reflectivity of low-energy electrons. Physical Review B, 2008, 77, .	3.2	330
3	Direct Chemical Vapor Deposition Growth of WS_2 Atomic Layers on Hexagonal Boron Nitride. ACS Nano, 2014, 8, 8273-8277.	14.6	267
4	Dependence of electronic properties of epitaxial few-layer graphene on the number of layers investigated by photoelectron emission microscopy. Physical Review B, 2009, 79, .	3.2	246
5	Carbon Nanotube Growth from Semiconductor Nanoparticles. Nano Letters, 2007, 7, 2272-2275.	9.1	224
6	Domain Structure and Boundary in Single-Layer Graphene Grown on Cu(111) and Cu(100) Films. Journal of Physical Chemistry Letters, 2012, 3, 219-226.	4.6	209
7	Quantum Faraday and Kerr rotations in graphene. Nature Communications, 2013, 4, 1841.	12.8	167
8	Growth and Optical Properties of High-Quality Monolayer WS_2 on Graphite. ACS Nano, 2015, 9, 4056-4063.	14.6	162
9	Catalytic Growth of Graphene: Toward Large-Area Single-Crystalline Graphene. Journal of Physical Chemistry Letters, 2012, 3, 2228-2236.	4.6	136
10	DC-Resistive-Heating-Induced Step Bunching on Vicinal Si (111). Japanese Journal of Applied Physics, 1990, 29, L2254-L2256.	1.5	126
11	Mechanism of Gold-Catalyzed Carbon Material Growth. Nano Letters, 2008, 8, 832-835.	9.1	112
12	Growth and low-energy electron microscopy characterization of monolayer hexagonal boron nitride on epitaxial cobalt. Nano Research, 2013, 6, 335-347.	10.4	108
13	Scalable synthesis of layer-controlled WS_2 and MoS_2 sheets by sulfurization of thin metal films. Applied Physics Letters, 2014, 105, .	3.3	107
14	Epitaxial few-layer graphene: towards single crystal growth. Journal Physics D: Applied Physics, 2010, 43, 374005.	2.8	106
15	Highly Uniform Bilayer Graphene on Epitaxial Cu-Ni (111) Alloy. Chemistry of Materials, 2016, 28, 4583-4592.	6.7	103
16	Anisotropic layer-by-layer growth of graphene on vicinal SiC (0001) surfaces. Physical Review B, 2010, 81, .	3.2	99
17	Influence of Cu metal on the domain structure and carrier mobility in single-layer graphene. Carbon, 2012, 50, 2189-2196.	10.3	86
18	Carrier transport mechanism in graphene on SiC (0001). Physical Review B, 2011, 84, .	3.2	85

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19	Stacking domains of epitaxial few-layer graphene on SiC(0001). <i>Physical Review B</i> , 2009, 80, .	3.2	84
20	High-temperature scanning-tunneling-microscopy observation of phase transitions and reconstruction on a vicinal Si(111) surface. <i>Physical Review B</i> , 1993, 47, 13027-13030.	3.2	74
21	Sublimation of the Si(111) surface in ultrahigh vacuum. <i>Physical Review B</i> , 1997, 55, R10237-R10240.	3.2	68
22	Growth Dynamics of Single-Layer Graphene on Epitaxial Cu Surfaces. <i>Chemistry of Materials</i> , 2015, 27, 5377-5385.	6.7	65
23	Half-Integer Quantum Hall Effect in Gate-Controlled Epitaxial Graphene Devices. <i>Applied Physics Express</i> , 2010, 3, 075102.	2.4	64
24	Surface-Mediated Aligned Growth of Monolayer MoS ₂ and In-Plane Heterostructures with Graphene on Sapphire. <i>ACS Nano</i> , 2018, 12, 10032-10044.	14.6	64
25	Theoretical Study of Epitaxial Graphene Growth on SiC(0001) Surfaces. <i>Applied Physics Express</i> , 0, 2, 065502.	2.4	62
26	In situ scanning electron microscopy of graphene growth on polycrystalline Ni substrate. <i>Surface Science</i> , 2012, 606, 728-732.	1.9	61
27	Decay kinetics of two-dimensional islands and holes on Si(111) studied by low-energy electron microscopy. <i>Physical Review B</i> , 2001, 63, .	3.2	60
28	Nonlinear terahertz field-induced carrier dynamics in photoexcited epitaxial monolayer graphene. <i>Physical Review B</i> , 2015, 91, .	3.2	60
29	Characterization of doped single-wall carbon nanotubes by Raman spectroscopy. <i>Carbon</i> , 2011, 49, 2264-2272.	10.3	55
30	Hydrogen storage with titanium-functionalized graphene. <i>Applied Physics Letters</i> , 2013, 103, .	3.3	55
31	Transient step bunching on a vicinal Si(111) surface. <i>Physical Review Letters</i> , 1994, 72, 657-660.	7.8	54
32	Dynamics of the silicon (111) surface phase transition. <i>Nature</i> , 2000, 405, 552-554.	27.8	53
33	Atmospheric Pressure Chemical Vapor Deposition Growth of Millimeter-Scale Single-Crystalline Graphene on the Copper Surface with a Native Oxide Layer. <i>Chemistry of Materials</i> , 2016, 28, 4893-4900.	6.7	52
34	Resonant Edge Magnetoplasmons and Their Decay in Graphene. <i>Physical Review Letters</i> , 2014, 113, 266601.	7.8	48
35	Fabrication and Integration of Nanostructures on Si Surfaces. <i>Accounts of Chemical Research</i> , 1999, 32, 447-454.	15.6	46
36	Thickness Determination of Graphene Layers Formed on SiC Using Low-Energy Electron Microscopy. <i>E-Journal of Surface Science and Nanotechnology</i> , 2008, 6, 107-110.	0.4	46

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37	Plasmon transport in graphene investigated by time-resolved electrical measurements. <i>Nature Communications</i> , 2013, 4, 1363.	12.8	46
38	Growth of atomically thin hexagonal boron nitride films by diffusion through a metal film and precipitation. <i>Journal Physics D: Applied Physics</i> , 2012, 45, 385304.	2.8	44
39	Spatially Controlled Nucleation of Single-Crystal Graphene on Cu Assisted by Stacked Ni. <i>ACS Nano</i> , 2016, 10, 11196-11204.	14.6	43
40	On-chip graphene oxide aptasensor for multiple protein detection. <i>Analytica Chimica Acta</i> , 2015, 866, 1-9.	5.4	42
41	Void growth during thermal decomposition of silicon oxide layers studied by low-energy electron microscopy. <i>Journal of Applied Physics</i> , 2006, 100, 113519.	2.5	38
42	Local conductance measurements of double-layer graphene on SiC substrate. <i>Nanotechnology</i> , 2009, 20, 445704.	2.6	38
43	Growth and electronic transport properties of epitaxial graphene on SiC. <i>Journal Physics D: Applied Physics</i> , 2012, 45, 154008.	2.8	38
44	Step arrangement design and nanostructure self-organization on Si surfaces. <i>Applied Surface Science</i> , 1997, 117-118, 642-651.	6.1	36
45	Mesh pattern of Ge islands grown using solid phase epitaxy. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 1993, 11, 2458-2462.	2.1	34
46	Shot noise generated by graphene p-n junctions in the quantum Hall effect regime. <i>Nature Communications</i> , 2015, 6, 8068.	12.8	34
47	Twinned epitaxial layers formed on Si(111)-B. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 1998, 16, 1934-1937.	2.1	33
48	Sublimation of a heavily boron-doped Si(111) surface. <i>Physical Review B</i> , 1998, 58, 13146-13150.	3.2	33
49	Site-controlled InP nanowires grown on patterned Si substrates. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2004, 24, 133-137.	2.7	33
50	Vertical GaP nanowires arranged at atomic steps on Si(111) substrates. <i>Applied Physics Letters</i> , 2006, 89, 033114.	3.3	33
51	Molecular design for enhanced sensitivity of a FRET aptasensor built on the graphene oxide surface. <i>Chemical Communications</i> , 2013, 49, 10346-10348.	4.1	32
52	Behavior and role of superficial oxygen in Cu for the growth of large single-crystalline graphene. <i>Applied Surface Science</i> , 2017, 408, 142-149.	6.1	32
53	Patterning-Assisted Control for Ordered Arrangement of Atomic Steps on Si(111) Surfaces. <i>Japanese Journal of Applied Physics</i> , 1995, 34, L668-L670.	1.5	31
54	Thin Graphitic Structure Formation on Various Substrates by Gas-Source Molecular Beam Epitaxy Using Cracked Ethanol. <i>Japanese Journal of Applied Physics</i> , 2010, 49, 04DH13.	1.5	30

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55	Graphene FRET Aptasensor. ACS Sensors, 2016, 1, 710-716.	7.8	30
56	Protein recognition on a single graphene oxide surface fixed on a solid support. Journal of Materials Chemistry B, 2013, 1, 1119.	5.8	29
57	Characterization of Optical Absorption and Polarization Dependence of Single-Layer Graphene Integrated on a Silicon Wire Waveguide. Japanese Journal of Applied Physics, 2013, 52, 060203.	1.5	29
58	Graphene nanoribbon field-effect transistors fabricated by etchant-free transfer from Au(788). Applied Physics Letters, 2018, 112, .	3.3	29
59	Electrical Characterization of Bilayer Graphene Formed by Hydrogen Intercalation of Monolayer Graphene on SiC(0001). Japanese Journal of Applied Physics, 2012, 51, 02BN02.	1.5	29
60	Quantum Hall Effect and Carrier Scattering in Quasi-Free-Standing Monolayer Graphene. Applied Physics Express, 2012, 5, 125101.	2.4	28
61	Graphene-Based Nano-Electro-Mechanical Switch with High On/Off Ratio. Applied Physics Express, 2013, 6, 055101.	2.4	28
62	Graphene-modified Interdigitated Array Electrode: Fabrication, Characterization, and Electrochemical Immunoassay Application. Analytical Sciences, 2013, 29, 55-60.	1.6	28
63	Isothermal Growth and Stacking Evolution in Highly Uniform Bernal-Stacked Bilayer Graphene. ACS Nano, 2020, 14, 6834-6844.	14.6	28
64	Arrangement of Au-Si alloy islands at atomic steps. Surface Science, 2005, 588, L233-L238.	1.9	27
65	Lattice-Oriented Catalytic Growth of Graphene Nanoribbons on Heteroepitaxial Nickel Films. ACS Nano, 2013, 7, 10825-10833.	14.6	27
66	Impact of graphene quantum capacitance on transport spectroscopy. Physical Review B, 2012, 86, .	3.2	26
67	Ultrathin Chemical Vapor Deposition (CVD)-Grown Hexagonal Boron Nitride as a High-Quality Dielectric for Tunneling Devices on Rigid and Flexible Substrates. Journal of Physical Chemistry C, 2014, 118, 3340-3346.	3.1	26
68	Fabrication of nanostructures on silicon surfaces on wafer scale by controlling self-organization processes. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1996, 14, 4134.	1.6	25
69	Chemical vapor deposition of boron- and nitrogen-containing graphene thin films. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2012, 177, 233-238.	3.5	25
70	Reflection High-Energy Electron Diffraction Studies of Vicinal Si(111) Surfaces. Japanese Journal of Applied Physics, 1991, 30, 1337-1342.	1.5	24
71	Hysteresis in the (1 $\bar{1}$ -1)-(7 $\bar{7}$ -7) first-order phase transition on the Si(111) surface. Surface Science, 2001, 487, 191-200.	1.9	24
72	Nonlinear transmission of an intense terahertz field through monolayer graphene. AIP Advances, 2014, 4, 117118.	1.3	24

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73	Reducing domain boundaries of surface reconstruction during molecular beam epitaxy on Si(111). <i>Applied Physics Letters</i> , 1995, 67, 915-917.	3.3	23
74	The physics of epitaxial graphene on SiC(0001). <i>Journal of Physics Condensed Matter</i> , 2012, 24, 314215.	1.8	23
75	Study of Graphene Growth by Gas-Source Molecular Beam Epitaxy Using Cracked Ethanol: Influence of Gas Flow Rate on Graphitic Material Deposition. <i>Japanese Journal of Applied Physics</i> , 2011, 50, 06GE12.	1.5	23
76	Phase transitions on Si(113): A high-temperature scanning-tunneling-microscopy study. <i>Physical Review B</i> , 1997, 56, 4092-4097.	3.2	22
77	Step wandering induced by homoepitaxy on Si(111) during $(1\times 1)-(7\times 7)$ phase transition. <i>Surface Science</i> , 2003, 527, L222-L228.	1.9	22
78	In-plane conductance measurement of graphene nanoislands using an integrated nanogap probe. <i>Nanotechnology</i> , 2008, 19, 495701.	2.6	22
79	Structural Instability of Transferred Graphene Grown by Chemical Vapor Deposition against Heating. <i>Journal of Physical Chemistry C</i> , 2013, 117, 22123-22130.	3.1	22
80	Design of Si surfaces for self-assembled nanoarchitecture. <i>Surface Science</i> , 2002, 514, 1-9.	1.9	21
81	Raman spectroscopic investigation of polycrystalline structures of CVD-grown graphene by isotope labeling. <i>Nanoscale</i> , 2014, 6, 13838-13844.	5.6	21
82	Catalyst-Selective Growth of Single-Orientation Hexagonal Boron Nitride toward High-Performance Atomically Thin Electric Barriers. <i>Advanced Materials</i> , 2019, 31, e1900880.	21.0	21
83	Real-Time Observation of $(1\times 1)-(7\times 7)$ Phase Transition on Vicinal Si(111) Surfaces by Scanning Tunneling Microscopy. <i>Japanese Journal of Applied Physics</i> , 1993, 32, 3247-3251.	1.5	20
84	Step arrangement design and nanostructure self-organization on Si(111) surfaces by patterning-assisted control. <i>Applied Surface Science</i> , 1996, 107, 1-5.	6.1	20
85	Two-dimensional emission patterns of secondary electrons from graphene layers formed on SiC(0001). <i>Applied Surface Science</i> , 2008, 254, 7596-7599.	6.1	20
86	Contact Conductance Measurement of Locally Suspended Graphene on SiC. <i>Applied Physics Express</i> , 2010, 3, 045101.	2.4	20
87	Self-spreading of Supported Lipid Bilayer on SiO ₂ Surface Bearing Graphene Oxide. <i>Chemistry Letters</i> , 2012, 41, 1259-1261.	1.3	20
88	Effects of hydrogen intercalation on transport properties of quasi-free-standing monolayer graphene. <i>Japanese Journal of Applied Physics</i> , 2014, 53, 04EN01.	1.5	20
89	Growth and low-energy electron microscopy characterizations of graphene and hexagonal boron nitride. <i>Progress in Crystal Growth and Characterization of Materials</i> , 2016, 62, 155-176.	4.0	20
90	Pb preadsorption facilitates island formation during Ge growth on Si(111). <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 1994, 12, 23-28.	2.1	19

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91	Correlation between morphology and transport properties of quasi-free-standing monolayer graphene. Applied Physics Letters, 2014, 105, 221604.	3.3	19
92	Influence of graphene on quality factor variation in a silicon ring resonator. Applied Physics Letters, 2014, 104, 091122.	3.3	19
93	Step band structures on vicinal Si(111) surfaces created by DC resistive heating. Applied Surface Science, 1992, 60-61, 479-484.	6.1	18
94	Real-space observation of (111) facet formation on vicinal Si(111) surfaces. Physical Review B, 1995, 51, 7753-7761.	3.2	18
95	Kinetics and Thermodynamics of Surface Steps on Semiconductors. Critical Reviews in Solid State and Materials Sciences, 1999, 24, 227-263.	12.3	18
96	Graphene Growth from a Spin-Coated Polymer without a Reactive Gas. Applied Physics Express, 2011, 4, 065102.	2.4	18
97	Macroscopic Single-Domain Graphene Growth on Polycrystalline Nickel Surface. Applied Physics Express, 2012, 5, 035501.	2.4	18
98	Surface structural changes during the initial growth of Ge on Si(111)7 Å—7. Applied Surface Science, 1992, 60-61, 112-119.	6.1	17
99	Disordering of Si(111) at high temperatures. Physical Review B, 1998, 58, 12587-12589.	3.2	17
100	Step wandering due to the gap in diffusion coefficient on the upper and the lower terraces. Surface Science, 2003, 522, 64-74.	1.9	17
101	Electrical Characterization of Bilayer Graphene Formed by Hydrogen Intercalation of Monolayer Graphene on SiC(0001). Japanese Journal of Applied Physics, 2012, 51, 02BN02.	1.5	17
102	Chemical Vapor Deposition of Hexagonal Boron Nitride. E-Journal of Surface Science and Nanotechnology, 2012, 10, 133-138.	0.4	17
103	On-chip FRET Graphene Oxide Aptasensor: Quantitative Evaluation of Enhanced Sensitivity by Aptamer with a Double-stranded DNA Spacer. Analytical Sciences, 2015, 31, 875-879.	1.6	17
104	Orientation-controlled growth of hexagonal boron nitride monolayers templated from graphene edges. Applied Physics Express, 2017, 10, 055102.	2.4	17
105	Effects of environmental conditions on the ultrafast carrier dynamics in graphene revealed by terahertz spectroscopy. Physical Review B, 2017, 95, .	3.2	17
106	Exchanges between group-III (B, Al, Ga, In) and Si atoms on Si(111)-3Å—3surfaces. Physical Review B, 1996, 54, 5763-5768.	3.2	16
107	Diffusion barrier caused by1Å—1and7Å—7on Si(111) during phase transition. Physical Review B, 2001, 64, .	3.2	16
108	Observation of Band Gap in Epitaxial Bilayer Graphene Field Effect Transistors. Japanese Journal of Applied Physics, 2011, 50, 04DN04.	1.5	16

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109	Stability and reactivity of steps in the initial stage of graphene growth on the SiC(0001) surface. <i>Physical Review B</i> , 2013, 88, .	3.2	16
110	Selective charge doping of chemical vapor deposition-grown graphene by interface modification. <i>Applied Physics Letters</i> , 2013, 103, .	3.3	16
111	Synthesis of sub-millimeter single-crystal grains of aligned hexagonal boron nitride on an epitaxial Ni film. <i>Nanoscale</i> , 2019, 11, 14668-14675.	5.6	16
112	Boron Nitride Thin Films Grown on Graphitized 6H-SiC Substrates by Metalorganic Vapor Phase Epitaxy. <i>Japanese Journal of Applied Physics</i> , 2007, 46, 2554-2557.	1.5	15
113	Boron nitride growth on metal foil using solid sources. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2013, 31, .	1.2	15
114	Tuning of quantum interference in top-gated graphene on SiC. <i>Physical Review B</i> , 2013, 88, .	3.2	15
115	Photocurrent generation of a single-gate graphene p-n junction fabricated by interfacial modification. <i>Nanotechnology</i> , 2015, 26, 385203.	2.6	15
116	Formation of twinned two-bilayer-high islands during initial stages of Si growth on Si(111)-B. <i>Surface Science</i> , 1998, 412-413, 132-140.	1.9	14
117	Instability of steps during Ga deposition on Si(111). <i>Surface Science</i> , 2008, 602, 2421-2426.	1.9	14
118	Probing the extended-state width of disorder-broadened Landau levels in epitaxial graphene. <i>Physical Review B</i> , 2015, 92, .	3.2	14
119	Energy Dissipation in Graphene Mechanical Resonators with and without Free Edges. <i>Micromachines</i> , 2016, 7, 158.	2.9	14
120	Atomic and electronic structure of Si dangling bonds in quasi-free-standing monolayer graphene. <i>Nano Research</i> , 2018, 11, 864-873.	10.4	14
121	Epitaxial Intercalation Growth of Scalable Hexagonal Boron Nitride/Graphene Bilayer Moiré Materials with Highly Convergent Interlayer Angles. <i>ACS Nano</i> , 2021, 15, 14384-14393.	14.6	14
122	Enhanced Terrace Stability for Preparation of Step-Free Si(001) $\sqrt{2} \times \sqrt{2} - 1$ Surfaces. <i>Physical Review Letters</i> , 2001, 87, 136103.	7.8	13
123	Molecular beam epitaxial growth of graphene and ridge-structure networks of graphene. <i>Journal Physics D: Applied Physics</i> , 2011, 44, 435305.	2.8	13
124	Site-Selective Epitaxy of Graphene on Si Wafers. <i>Proceedings of the IEEE</i> , 2013, 101, 1557-1566.	21.3	13
125	Epitaxial Trilayer Graphene Mechanical Resonators Obtained by Electrochemical Etching Combined with Hydrogen Intercalation. <i>Japanese Journal of Applied Physics</i> , 2013, 52, 04CH01.	1.5	13
126	Energy dissipation in edged and edgeless graphene mechanical resonators. <i>Journal of Applied Physics</i> , 2014, 116, 064304.	2.5	13

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127	Growth of Si twinning superlattice. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2001, 87, 214-221.	3.5	12
128	Epitaxial Graphene Growth Studied by Low-Energy Electron Microscopy and First-Principles. <i>Materials Science Forum</i> , 0, 645-648, 597-602.	0.3	12
129	Core-level photoelectron spectroscopy study of interface structure of hydrogen-intercalated graphene on n-type 4H-SiC(0001). <i>Physical Review B</i> , 2013, 88, .	3.2	12
130	Graphene Layer Formation on Polycrystalline Nickel Grown by Chemical Vapor Deposition. <i>Japanese Journal of Applied Physics</i> , 2013, 52, 035103.	1.5	12
131	Real-time scanning tunneling microscopy of phase transition and faceting on a vicinal Si(111) surface. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 1993, 11, 1640-1643.	2.1	11
132	Trace of interface reconstruction in Ge solid-phase epitaxy on Si(111). <i>Physical Review B</i> , 1994, 49, 5765-5768.	3.2	11
133	Exchanges between Si and Pb adatoms on Si(111). <i>Surface Science</i> , 1995, 328, L547-L552.	1.9	11
134	Substitution of In for Si adatoms and exchanges between In and Si adatoms on a Si(111)- $\sqrt{7}\times\sqrt{7}$ surface. <i>Physical Review B</i> , 1997, 55, 7018-7022.	3.2	11
135	Molecular beam epitaxial growth of graphene using cracked ethylene " Advantage over ethanol in growth. <i>Diamond and Related Materials</i> , 2013, 34, 84-88.	3.9	11
136	<i>In situ</i> scanning electron microscopy of graphene nucleation during segregation of carbon on polycrystalline Ni substrate. <i>Journal Physics D: Applied Physics</i> , 2014, 47, 455301.	2.8	11
137	Etchant-free graphene transfer using facile intercalation of alkanethiol self-assembled molecules at graphene/metal interfaces. <i>Nanoscale</i> , 2016, 8, 11503-11510.	5.6	11
138	Atomic Structure and Physical Properties of Epitaxial Graphene Islands Embedded in SiC(0001) Surfaces. <i>Applied Physics Express</i> , 2010, 3, 115103.	2.4	10
139	Plasmon transport and its guiding in graphene. <i>New Journal of Physics</i> , 2014, 16, 063055.	2.9	10
140	Etchant-free and damageless transfer of monolayer and bilayer graphene grown on SiC. <i>Japanese Journal of Applied Physics</i> , 2014, 53, 115101.	1.5	10
141	Controlled CVD growth of lateral and vertical graphene/h-BN heterostructures. <i>Applied Physics Express</i> , 2020, 13, 065007.	2.4	10
142	Direct evidence for Ge preferential growth at steps and out-of-phase boundaries of ($\sqrt{7}\times\sqrt{7}$) domains on Si(111) in solid phase epitaxy. <i>Surface Science</i> , 1995, 324, L333-L336.	1.9	9
143	$\sqrt{1}\times\sqrt{1}$ to ($\sqrt{7}\times\sqrt{7}$) phase transition on Si(111) under heating current. <i>Surface Science</i> , 1996, 364, L587-L590.		9
144	Two-stage phase transition of $\sqrt{12}\times\sqrt{1}$ reconstruction on Si(331). <i>Physical Review B</i> , 1996, 53, 15682-15687.	3.2	9

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145	Triangular-tiled arrangement of $7\sqrt{3}\text{Å}$ and $1\sqrt{3}\text{Å}$ domains on Si(111). <i>Physical Review B</i> , 1998, 58, R7500-R7503.		9
146	Growth of Twinned Epitaxial Layers on Si(111)-B Studied by Low-Energy Electron Microscopy. <i>Japanese Journal of Applied Physics</i> , 2005, 44, 358-364.	1.5	9
147	Formation of Oriented Graphene Nanoribbons over Heteroepitaxial Cu Surfaces by Chemical Vapor Deposition. <i>Chemistry of Materials</i> , 2014, 26, 5215-5222.	6.7	9
148	Quantum Hall effect in epitaxial graphene with permanent magnets. <i>Scientific Reports</i> , 2016, 6, 38393.	3.3	9
149	Ultra-fine metal gate operated graphene optical intensity modulator. <i>Applied Physics Letters</i> , 2016, 109, .	3.3	9
150	Grain Boundaries and Gas Barrier Property of Graphene Revealed by Dark-Field Optical Microscopy. <i>Journal of Physical Chemistry C</i> , 2018, 122, 902-910.	3.1	9
151	A Lattice Model for Thermal Decoration and Step Bunching in Vicinal Surface with Sub-Monolayer Adsorbates. <i>E-Journal of Surface Science and Nanotechnology</i> , 2009, 7, 39-44.	0.4	9
152	Evaluation of Few-Layer Graphene Grown by Gas-Source Molecular Beam Epitaxy Using Cracked Ethanol. <i>E-Journal of Surface Science and Nanotechnology</i> , 2011, 9, 58-62.	0.4	9
153	Theoretical Study on Magnetoelectric and Thermoelectric Properties for Graphene Devices. <i>Japanese Journal of Applied Physics</i> , 2011, 50, 070115.	1.5	9
154	Theoretical Study on Epitaxial Graphene Growth by Si Sublimation from SiC(0001) Surface. <i>Japanese Journal of Applied Physics</i> , 2011, 50, 095601.	1.5	9
155	Scanning tunneling microscopy observations of Ge solid-phase epitaxy on Si(111). <i>Applied Surface Science</i> , 1994, 82-83, 374-379.	6.1	8
156	Thermal decay of superheated $7\sqrt{3}\text{Å}$ islands and supercooled $1\sqrt{3}\text{Å}$ vacancy islands on Si(111). <i>Physical Review B</i> , 2005, 72, .	3.2	8
157	Local conductance measurement of few-layer graphene on SiC substrate using an integrated nanogap probe. <i>Journal of Physics: Conference Series</i> , 2008, 100, 052006.	0.4	8
158	Theoretical Study on Magnetoelectric and Thermoelectric Properties for Graphene Devices. <i>Japanese Journal of Applied Physics</i> , 2011, 50, 070115.	1.5	8
159	Study of Graphene Growth by Gas-Source Molecular Beam Epitaxy Using Cracked Ethanol: Influence of Gas Flow Rate on Graphitic Material Deposition. <i>Japanese Journal of Applied Physics</i> , 2011, 50, 06GE12.	1.5	8
160	Theoretical Study on Epitaxial Graphene Growth by Si Sublimation from SiC(0001) Surface. <i>Japanese Journal of Applied Physics</i> , 2011, 50, 095601.	1.5	8
161	Direct growth of graphene on SiC(0001) by KrF-excimer-laser irradiation. <i>Applied Physics Letters</i> , 2016, 108, 093107.	3.3	8
162	Growth process of twinned epitaxial layers on Si(111)-B and their thermal stability. <i>Applied Surface Science</i> , 1998, 130-132, 41-46.	6.1	7

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163	Controlled striped phase formation on ultraflat Si(001) surfaces during diborane exposure. Applied Physics Letters, 2001, 79, 3857-3859.	3.3	7
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